

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	48617	(soi silicon-on-insulator silicon adj insulator thin adj film adj transistor\$2 tft lod alelectrol \$1luminesc\$5).ti,dlm,ab.	US-PGPUB; USPAT	OR	ON	2008/09/12 18:33
L2	13674	(cap\$1ing cap) adj (region layer portion)and (spacer side \$1wall)	US-PGPUB; USPAT	OR	ON	2008/09/12 18:34
L3	115	1 and 2 and (ldd low\$2 adj impurity mdd)	US-PGPUB; USPAT	OR	OFF	2008/09/12 18:34
L4	29	((@ad<="20020208" @rlad<="20020208") and 3	USPAT	OR	OFF	2008/09/12 18:35
L5	54	((@ad<="20020208" @rlad<="20020208") and 3	US-PGPUB; USPAT	OR	OFF	2008/09/12 18:35
L6	453	(reduc\$4 decreas\$4 lower\$4) near3 (interconnect adj resistance)	US-PGPUB; USPAT	OR	ON	2008/09/12 18:37
L7	0	1 and 2 and 6	US-PGPUB; USPAT	OR	OFF	2008/09/12 18:37
L8	260495	(soi silicon-on-insulator silicon adj insulator thin adj film adj transistor\$2 tft lod alelectrol \$1luminesc\$5)	US-PGPUB; USPAT	OR	ON	2008/09/12 18:37
L9	11	8 and 2 and 6	US-PGPUB; USPAT	OR	OFF	2008/09/12 18:38
L10	71392	(source drain)adj (contact\$2 electrode\$2 wiring\$2)	US-PGPUB; USPAT	OR	ON	2008/09/12 18:42
L11	98	(reduc\$4 decreas\$4 lower\$4) near3 (interconnect adj resistance) and 10	US-PGPUB; USPAT	OR	ON	2008/09/12 18:42
L12	37	((@ad<="20020208" @rlad<="20020208") and 11	US-PGPUB; USPAT	OR	OFF	2008/09/12 18:43
L13	173	1 and 2 and 10	US-PGPUB; USPAT	OR	OFF	2008/09/12 18:45
L14	91	((@ad<="20020208" @rlad<="20020208") and 13	US-PGPUB; USPAT	OR	OFF	2008/09/12 18:45
L15	91	14 not 12	US-PGPUB; USPAT	OR	OFF	2008/09/12 18:45
L16	53	14 not 5	US-PGPUB; USPAT	OR	OFF	2008/09/12 18:45
L17	53	(cap\$1ing cap) and 16	US-PGPUB; USPAT	OR	ON	2008/09/12 18:47
L18	0	17 and (ldd low\$2 adj impurity mdd)	US-PGPUB; USPAT	OR	OFF	2008/09/12 18:48
L19	41515	(source drain)adj (contact\$2 electrode\$2 wiring\$2)	EPO, JPO, DERWENT	OR	ON	2008/09/12 18:48

L20	600	(cap\$1ing cap) and 19	EPO; JPO; DERWENT	OR	ON	2008/09/12 18:48
L21	3	20 and (ldd low\$2 adj impurity mdd)	EPO; JPO; DERWENT	OR	OFF	2008/09/12 18:49
L22	25	(reduc\$4 decreas\$4 lower\$4) near3 (interconnect adj resistance)	EPO; JPO; DERWENT	OR	ON	2008/09/12 18:50
L23	0	22 and 19	EPO; JPO; DERWENT	OR	ON	2008/09/12 18:50
L24	205926	(soi silicon-on-insulator silicon adj insulator thin adj film adj transistor\$2 tft lod aleletrol \$1luminesc\$5)	EPO; JPO; DERWENT	OR	ON	2008/09/12 18:51
L25	1	22 and 24	EPO; JPO; DERWENT	OR	ON	2008/09/12 18:51
L26	70	20 and 24	EPO; JPO; DERWENT	OR	OFF	2008/09/12 18:51
L27	604	257/E21.605 257/E27.111 257/E29.003.ccls.	EPO; JPO	OR	ON	2008/09/12 18:53
L28	0	22 and 27	EPO; JPO; DERWENT	OR	ON	2008/09/12 18:54
L29	0	(cap\$1ing cap) and 19 and 27	EPO; JPO; DERWENT	OR	ON	2008/09/12 18:54
L30	86	19 and 27	EPO; JPO; DERWENT	OR	ON	2008/09/12 18:54
L31	0	30 and (ldd low\$2 adj impurity mdd)	EPO; JPO; DERWENT	OR	OFF	2008/09/12 18:54
L32	56	30 and 24	EPO; JPO; DERWENT	OR	ON	2008/09/12 18:55
L33	351	(source drain)adj (contact\$2 electrode\$2 wiring\$2)adj3 direct\$4	EPO; JPO; DERWENT	OR	ON	2008/09/12 18:57
L34	0	33 and 27	EPO; JPO; DERWENT	OR	ON	2008/09/12 18:57
L35	5	33 and (ldd low\$2 adj impurity mdd)	EPO; JPO; DERWENT	OR	OFF	2008/09/12 18:57
L36	882	(source drain)adj (contact\$2 electrode\$2 wiring\$2)adj3 directly	US-PGPUB; USPAT	OR	ON	2008/09/12 18:58
L37	5702	257/E21.605 257/E27.111 257/E29.003.ccls.	US-PGPUB; USPAT	OR	ON	2008/09/12 18:58
L38	83	36 and 37	US-PGPUB; USPAT	OR	ON	2008/09/12 18:58
L39	17	((@ad<="20020208" @rlad<="20020208") and 38	US-PGPUB; USPAT	OR	OFF	2008/09/12 18:58
L40	1147	257/72 257/59 257/347 438/149 438/479 438/517 438/48.ccls.	EPO; JPO	OR	ON	2008/09/12 19:01

L41	11694	257/72 257/59 257/347 438/149 438/479 438/517 438/48.ccls.	US-PGPUB; USPAT	OR	ON	2008/09/12 19:01
L42	5675	((@ad<="20020208" @rlad<="20020208") and 41	US-PGPUB; USPAT	OR	OFF	2008/09/12 19:01
L43	81	((@pd>="20080116") and 42	US-PGPUB; USPAT	OR	OFF	2008/09/12 19:02

9/ 12/ 08 7:03:22 PM

C:\Documents and Settings\Asefer\My Documents\EAST\Workspaces\10068004.wsp